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Title: **JP61224423A2: REACTIVE ION ETCHING APPRATUS**

Derwent Title: Reactive ion etching device - includes material around the wafer being etched which can reduce the quantity of etching speeds at the same rate as the wafer [\[Derwent Record\]](#)

Country: JP Japan

Kind: A

Inventor: KATSURA TOSHIHIKO;
ABE MASAYASU;
TAKAOKI KIYOSHI;
AOYAMA MASA HARU;

Assignee: TOSHIBA CORP
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Published / Filed: 1986-10-06 / 1985-03-29

Application Number: JP1985000065407

IPC Code: [H01L 21/302](#);

Priority Number: 1985-03-29 JP1985000065407

Abstract: PURPOSE: To enable the wafer surface to be etched by a method wherein a material to reduce the etching species of reactive gas in the ratio almost the

CONSTITUTION: The facing of an electrode 6 and an insulating sheet 10 are made larger than the outside diameter of a semiconductor 8 which a correcting ring 20 is provided between a step difference 12 due to the facing and the semiconductor wafer 8. Any material able to reduce etching species of reactive gas in the ratio subject to the difference between the etched materials but at least almost the same as that of any etched materials is applicable to the correcting ring 20. In such a constitution, there is a material to reduce the etching element in the peripheral part of semiconductor wafer as well as on the semiconductor wafer therefore the apart subject to uneven concentration of etching species (a) can be shifted to outside making the concentration of etching even on the semiconductor wafer 8. Resultantly, the semiconductor wafer 8 can be etched evenly.

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References:

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	US6171974	2001-01-09	Marks; Jeffrey	Applied Materials, Inc.	High selectivity oxide e for integrated circuit str
	US5951814	1999-09-14	Saito; Kazuo	Nisshinbo Industries, Inc.	Electrode for plasma et
	US5681419	1997-10-28	Yoon; Hak-Soon	Hyundai Electronics Industries Co., Ltd.	Reactive ion etching ap
	US5556500	1996-09-17	Hasegawa; Makoto	Tokyo Electron Limited	Plasma etching appara
	US5330607	1994-07-19	Nowicki; Ronald S.	Genus, Inc.	Sacrificial metal etchba
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Other Abstract
Info:

DERABS C86-302121 DERC86-302121



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